

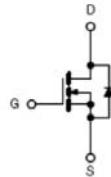


2300 MOSFET(N-Channel)

SOT-23 Plastic-Encapsulate Transistors

FEATURES

TrenchFET Power MOSFET

**SOT-23**

1. GATE
2. SOURCE
3. DRAIN

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

| Symbol | Parameter | Value | Units |
|------------------|----------------------|---------|-------|
| V _{DS} | Drain-Source voltage | 20 | V |
| V _{Gs} | Gate-Source voltage | ±10 | V |
| I _D | Drain current | 2.9 | A |
| P _D | Power Dissipation | 1 | W |
| T _j | Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature | -55-150 | °C |

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | TYP | MAX | UNIT |
|------------------------------------|----------------------|---|-----|------|------|------|
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | V _{Gs} =0V, I _D =250μA | 20 | | | V |
| Gate-Threshold Voltage | V _{th(gs)} | V _{DS} = V _{Gs} , I _D =250 μA | 0.5 | 0.75 | 1.2 | V |
| Gate-body Leakage | I _{GSS} | V _{DS} =0V, V _{Gs} =±10V | | | ±100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =20V, V _{Gs} =0V | | | 1 | uA |
| Drain-Source On-Resistance | r _{DS(ON)} | V _{Gs} =2. 5V, I _D =2.5A | | 37 | 59 | mΩ |
| | | V _{Gs} =4. 5V, I _D =2.9A | | 30 | 45 | mΩ |
| Forward Trans conductance | g _{fs} | V _{DS} =5V, I _D =2.9A | | 9.5 | | s |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =10V, V _{Gs} =0V, f=1MHz | | 300 | | pF |
| Output Capacitance | C _{oss} | | | 120 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 80 | | |
| Switching Capacitance | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DD} =10V, I _D =2. 9A, V _{Gs} =4. 5V R _{GEN} =6 Ω | | 10 | 15 | nS |
| Turn-on Rise Time | t _r | | | 50 | 85 | nS |
| Turn-off Delay Time | t _{d(off)} | | | 17 | 45 | nS |
| Turn-off Fall Time | t _f | | | 10 | 20 | nS |
| Total Gate Charge | Q _g | V _{DS} =10V, I _D =2. 9A, V _{Gs} =4. 5V, | | 4.0 | 10 | nC |
| Gate-Source Charge | Q _{gs} | | | 0.65 | | nC |
| Gate-Drain Charge | Q _{gd} | | | 1.2 | | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage | V _{SD} | V _{Gs} =0V, I _S =2. 9A | | 0.75 | 1.2 | V |
| Diode Forward Current | I _S | | | | 2.9 | A |

Typical Characteristics

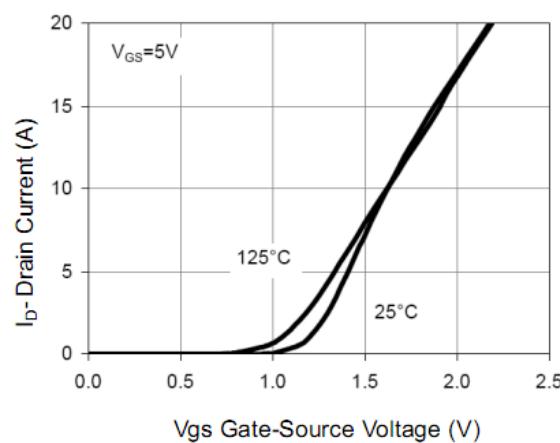


Figure 7 Transfer Characteristics

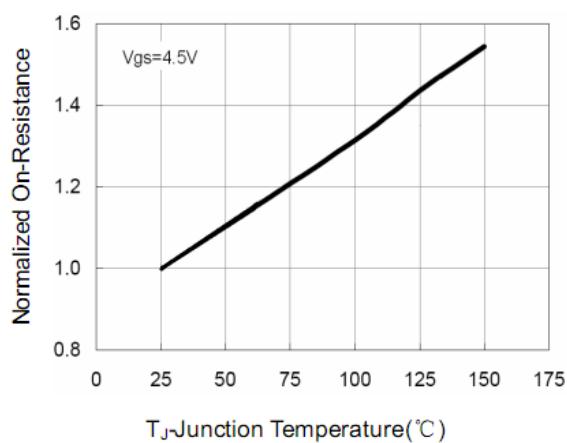


Figure 8 Drain-Source On-Resistance

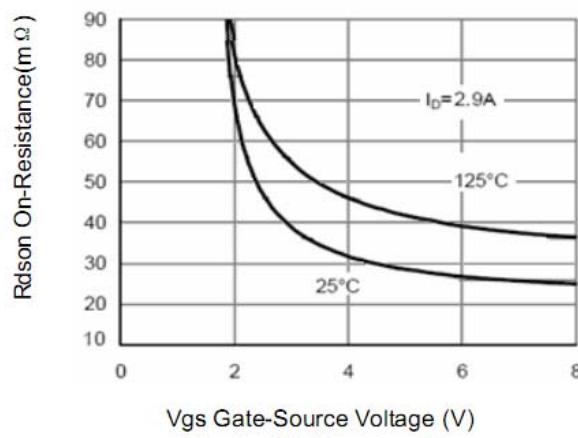
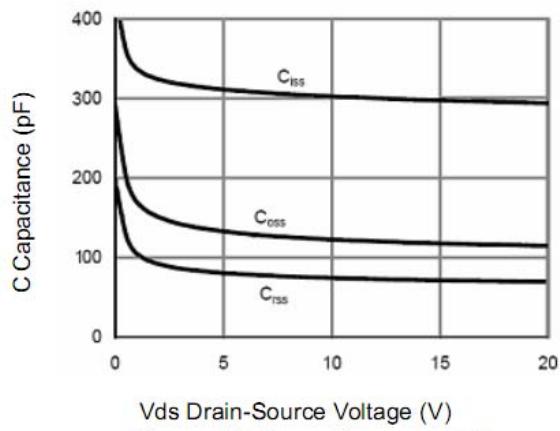
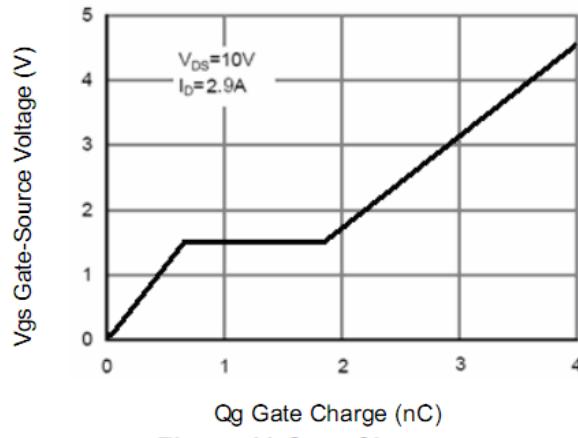
Figure 9 $R_{DS(on)}$ vs V_{GS} Figure 10 Capacitance vs V_{DS} 

Figure 11 Gate Charge

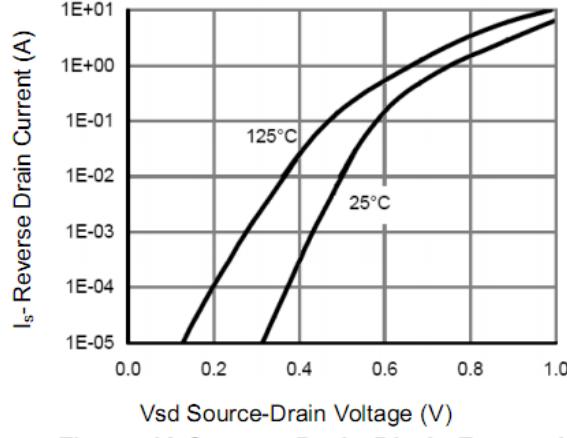


Figure 12 Source-Drain Diode Forward